FLAT-BASE TYPE INSULATED PACKAGE

PM100CL1A060



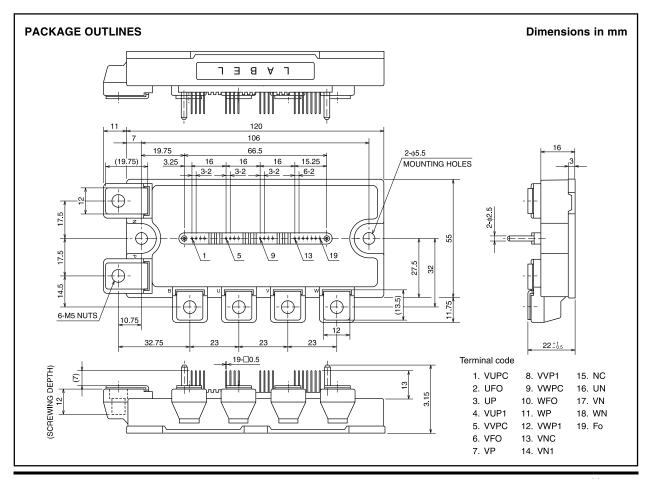
FEATURE

Inverter + Drive & Protection IC

- a) Adopting new 5th generation Full-Gate CSTBTTM chip
- b) The over-temperature protection which detects the chip surface temperature of $\mathsf{CSTBT^{TM}}$ is adopted.
- c) Error output signal is possible from all each protection upper and lower arm of IPM.
- d) Compatible L-series package.
 - 3φ 100A, 600V Current-sense and temperature sense IGBT type inverter
 - Monolithic gate drive & protection logic
 - Detection, protection & status indication circuits for, shortcircuit, over-temperature & under-voltage (P-Fo available from upper arm devices)
 - UL Recognized

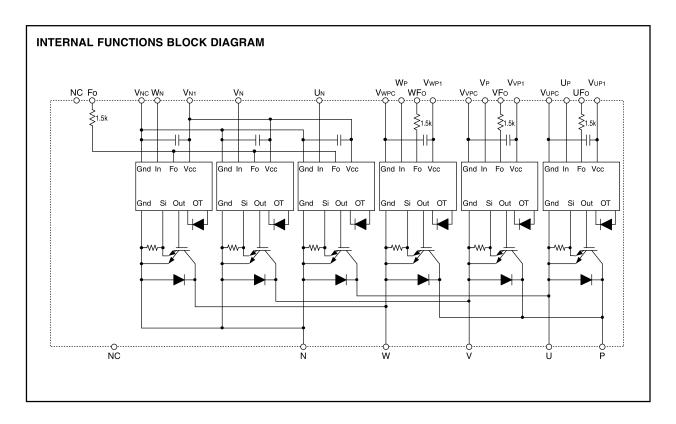
APPLICATION

General purpose inverter, servo drives and other motor controls





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MAXIMUM RATINGS (Tj = 25° C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition		Ratings	Unit
VCES	Collector-Emitter Voltage	VD = 15V, VCIN = 15V		600	V
±Ιc	Collector Current	Tc = 25°C	(Note-1)	100	Α
±ICP	Collector Current (Peak)	Tc = 25°C		200	Α
Pc	Collector Dissipation	Tc = 25°C	(Note-1)	390	W
Tj	Junction Temperature			−20 ~ +150	°C

^{*:} Tc measurement point is just under the chip.

CONTROL PART

Symbol	Parameter	Condition	Ratings	Unit
VD	Supply Voltage	Applied between: VuP1-VuPc, VvP1-VvPc VwP1-VwPc, Vn1-Vnc	20	V
VCIN	Input Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC UN • VN • WN-VNC	20	٧
VFO	Fault Output Supply Voltage	Applied between : UFO-VUPC, VFO-VVPC, WFO-VWPC FO-VNC	20	V
IFO	Fault Output Current	Sink current at UFO, VFO, WFO, FO terminals	20	mA



FLAT-BASE TYPE INSULATED PACKAGE

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Supply Voltage Protected by SC	V _D = 13.5 ~ 16.5V Inverter Part, T _j = +125°C Start	400	V
VCC(surge)	Supply Voltage (Surge)	Applied between : P-N, Surge value	500	V
Tstg	Storage Temperature		− 40 ~ +125	°C
Viso	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base, AC 1 min.	2500	Vrms

THERMAL RESISTANCES

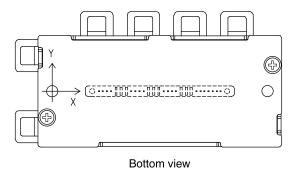
		O a madiki a m		Limits			
Symbol Parameter		Condition		Тур.	Max.	Unit	
Rth(j-c)Q	Junction to case Thermal	Inverter IGBT part (per 1 element) (Note-1		_	0.32		
Rth(j-c)F	Resistances	Inverter FWDi part (per 1 element) (Note-1		_	0.52	00044	
Rth(c-f)	Contact Thermal Resistance	Case to fin, (per 1 module)			0.000	°C/W	
		Thermal grease applied (Note-1	_	_	0.038		

^{*} If you use this value, Rth(f-a) should be measured just under the chips.

(Note-1) Tc (under the chip) measurement point is below.

(unit: mm)

	arm	U	Р	V	P	W	/P	U	N	V	N	W	N
axis		IGBT	FWDi										
Х		28.6	28.6	65.4	65.4	87.4	87.4	38.6	38.6	54.6	54.6	76.6	76.6
Υ		-9.0	-0.4	-9.0	-0.4	-9.0	-0.4	6.5	-1.1	6.5	-1.1	6.5	-1.1



ELECTRICAL CHARACTERISTICS ($T_j = 25^{\circ}C$, unless otherwise noted) **INVERTER PART**

0	Б	Condition			Unit		
Symbol	Parameter	Condition	Condition			Max.	Offic
Mart is	Collector-Emitter Saturation	VD = 15V, IC = 100A	Tj = 25°C	_	1.75	2.35	V
VCE(sat)	Voltage	VCIN = 0V, Pulsed (Fig. 1)	Tj = 125°C	_	1.75	2.35]
VEC	FWDi Forward Voltage	-IC = 100A, VD = 15V, VCIN = 15V	_	1.7	2.8	V	
ton		V- 45V V 0V 45V		0.3	0.8	2.0	
trr		VD = 15V, VCIN = 0V↔15V		_	0.4	0.8	
tc(on)	Switching Time	Vcc = 300V, lc = 100A		_	0.4	1.0	μs
toff		Tj = 125°C	(F: 0.4)	_	1.0	2.3	
tc(off)		Inductive Load	(Fig. 3,4)	_	0.3	1.0	
ICES Collector-Emitter Cutoff Current	Collector-Emitter Cutoff	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	Tj = 25°C	_	_	1	4
	Current	VCE = VCES, VD = 15V (Fig. 5)	Tj = 125°C	_	_	10	mA



FLAT-BASE TYPE INSULATED PACKAGE

CONTROL PART

0	Б.	O a statistica sa			1.1		
Symbol	Parameter	Condition		Min.	Тур.	Max.	Unit
lD	Circuit Current	VD = 15V, VCIN = 15V	VN1-VNC	_	6	12	m 1
טו	Circuit Current	VD = 13V, VCIN = 13V	V*P1-V*PC	_	2	4	mA
Vth(ON)	Input ON Threshold Voltage	Applied between : UP-VuPC, VP-VvPC,	WP-VWPC	1.2	1.5	1.8	V
Vth(OFF)	Input OFF Threshold Voltage	Un • Vn • Wn-Vnc		1.7	2.0	2.3	\ \
SC	Short Circuit Trip Level	-20 ≤ Tj ≤ 125°C, VD = 15V	(Fig. 3,6)	200	_	_	Α
toff(SC)	Short Circuit Current Delay Time	VD = 15V	(Fig. 3,6)	_	0.2	_	μs
ОТ	Over Temperature Protection	Detect Temperature of IGBT chip	Trip level	135	_	_	°C
OT(hys)	Over remperature Protection		Hysteresis	_	20	_	
UV	Supply Circuit Under-Voltage	_20 ≤ T _i ≤ 125°C	Trip level	11.5	12.0	12.5	V
UVr	Protection	-20 \(\)	Reset level	_	12.5	_	\ \ \
IFO(H)	Fault Output Current	VD = 15V, VCIN = 15V	(Note-2)	_	_	0.01	mA
IFO(L)	Fault Output Current	VD = 13V, VCIN = 13V	(14016-2)	_	10	15	'''
tFO	Minimum Fault Output Pulse Width	VD = 15V	(Note-2)	1.0	1.8	_	ms

(Note-2) Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

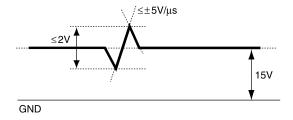
MECHANICAL RATINGS AND CHARACTERISTICS

	Description	Condition		Unit			
Symbol Parameter		Condition		Min.	Тур.	Max.	Onit
_	Mounting torque	Mounting part screen	w : M5	2.5	3.0	3.5	N • m
-		Main terminal part screen	w : M5	2.5	3.0	3.5	
_	Weight	-		_	380	_	а

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Condition	Recommended value	Unit
Vcc	Supply Voltage	Applied across P-N terminals	≤ 400	V
VD	Control Supply Voltage	Applied between: VuP1-VuPC, VvP1-VvPC VwP1-VwPC, Vn1-VnC (Note-3)	15.0 ± 1.5	٧
VCIN(ON)	Input ON Voltage	Applied between: UP-VUPC, VP-VVPC, WP-VWPC	≤ 0.8	V
VCIN(OFF)	Input OFF Voltage	Un • Vn • Wn-Vnc	≥ 9.0	V
fPWM	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
tdead	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 2.0	μs

(Note-3) With ripple satisfying the following conditions: dv/dt swing $\leq \pm 5V/\mu s$, Variation $\leq 2V$ peak to peak



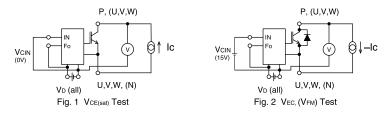


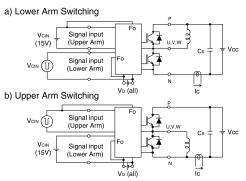
FLAT-BASE TYPE INSULATED PACKAGE

PRECAUTIONS FOR TESTING

- 1. Before applying any control supply voltage (VD), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state. After this, the specified ON and OFF level setting for each input signal should be done.
- 2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above VCES rating of the device.

(These test should not be done by using a curve tracer or its equivalent.)





90% 90% 10% 10% tc(on) td(on) td(off) (ton = td(on) + tr)(toff = td(off) + tf)

Fig. 3 Switching time and SC test circuit

Fig. 4 Switching time test waveform

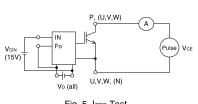


Fig. 5 Ices Test

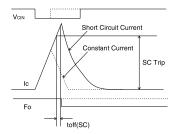
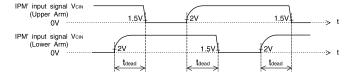


Fig. 6 SC test waveform



1.5V: Input on threshold voltage Vth(on) typical value, 2V: Input off threshold voltage Vth(off) typical value

Fig. 7 Dead time measurement point example



FLAT-BASE TYPE INSULATED PACKAGE

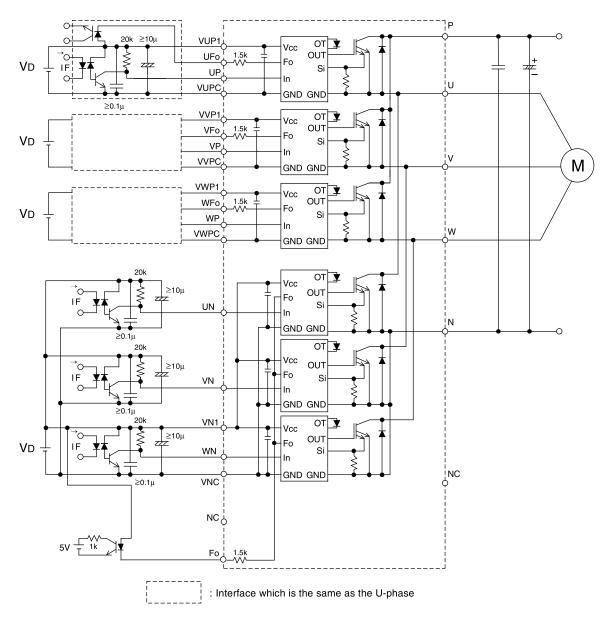


Fig. 8 Application Example Circuit

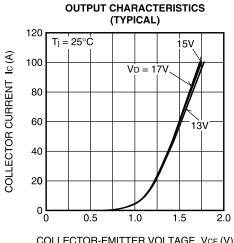
NOTES FOR STABLE AND SAFE OPERATION;

- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- ●Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: tPLH, tPHL ≤ 0.8μs, Use High CMR type.
- ●Slow switching opto-coupler: CTR > 100%
- Use 4 isolated control power supplies (VD). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.
- Use line noise filter capacitor (ex. 4.7nF) between each input AC line and ground to reject common-mode noise from AC line and improve noise immunity of the system.



FLAT-BASE TYPE INSULATED PACKAGE

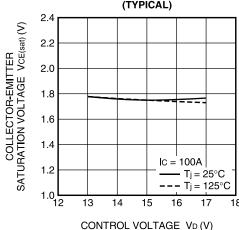
PERFORMANCE CURVES

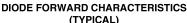


COLLECTOR-EMITTER SATURATION VOLTAGE (VS. Ic) CHARACTERISTICS (TYPICAL) 2.0 VD = 15V COLLECTOR-EMITTER SATURATION VOLTAGE VCE(sat) (V) 1.6 1.4 1.2 1.0 0.8 0.6 0.4 $T_j = 25^{\circ}C$ 0.2 - - Tj = 125°C 0 6 20 60 100 40 80

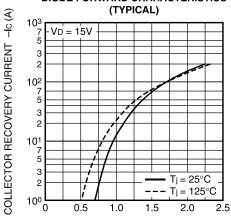
COLLECTOR-EMITTER VOLTAGE VCE (V)





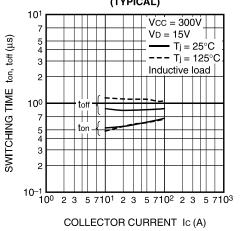


COLLECTOR CURRENT Ic (A)

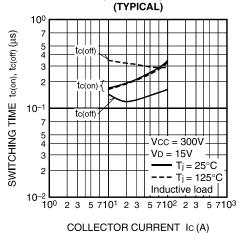


EMITTER-COLLECTOR VOLTAGE VEC (V)

SWITCHING TIME (ton, toff) CHARACTERISTICS (TYPICAL)



SWITCHING TIME (tc(on), tc(off)) CHARACTERISTICS



May 2009



FLAT-BASE TYPE INSULATED PACKAGE

(TYPICAL) 6.0 Eoff (mJ/pulse) Vcc = 300V 5.5 VD = 15V 5.0 - Tj = 25°C 4.5 **---** Tj = 125°C Inductive load 4.0 Eou, 3.5 3.0 SWITCHING LOSS 2.5 2.0 1.5

1.0

0.5

0

SWITCHING LOSS CHARACTERISTICS

60 COLLECTOR CURRENT Ic (A)

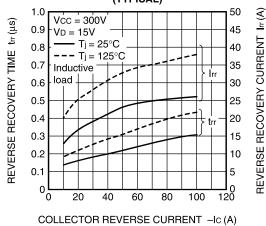
80

40

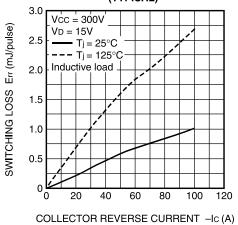
120

100

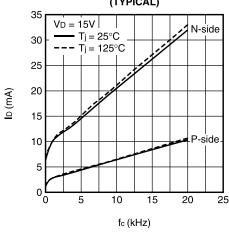
DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



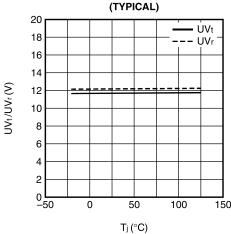
SWITCHING RECOVERY LOSS CHARACTERISTICS (TYPICAL)



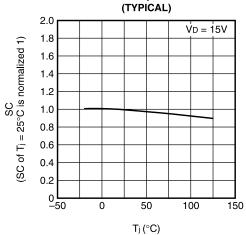
ID VS. fc CHARACTERISTICS (TYPICAL)



UV TRIP LEVEL VS. Ti CHARACTERISTICS



SC TRIP LEVEL VS. Ti CHARACTERISTICS





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TIME t (sec)



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